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UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,812,087 B2
DATED : November 2, 2004
INVENTOR(S) : Terry L. Gilton et al.

Page 1 of 3

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page.

Item [75], Inventors, "Giltom" should read -- Gilton --

Item [56], **References Cited**, U.S. PATENT DOCUMENTS, insert
-- 6,423,628 B1 7/2002 Li et al.

6,473,332 10/2002 Ignatiev et al. --

"Miyatani, Electrical properties of Ag₂Se, —J. Phys. Soc. Japan, p. 317, 1958." should read --Miyatani, Electrical Properties of Ag₂Se, 13 J. Phys. Soc. Japan, p. 317,1958. --

"Safran et al, "TEM study of Ag₂Se developed by the reaction of polycrystalline silver films and s I nium," 317 Thin Solid Films, pp. 72-76, 1998." should read -- Safran et al., "TEM study of Ag₂Se developed by the reaction of polycrystalline silver films and selenium," 317 Thin Solid Films, pp. 72-76,1998. --

"Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and ch mical thr sholds in IV-VI chalcogenide glasses, Phys. R v. L 62 (1989) 808410." should read -- Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, Phys. Rev. Lett, 62 (1989) 808-410.--

"Br ss r, W.J.; Boolchand, P.; Suranyl, P.; Hernandez, J.G., Molecular phase separation and cluster siz In G S 2 glass, Hyperfine Interactions 27 (1986) 389-392." should read -- Bresser, W.J.; Boolchand, P.; Suranyi, P.; Hernandez, J.G., Molecular phase separation and cluster size in GeSe₂ glass, Hyperfine Interactions 27 (1986) 389-392.--

"Cahen, D.; Gilet, J.-M.; Schmitz, C.; Ch rnyak, L.; Gartsman, K.; Jakubowicz, A., Room-Temperature, electric field induced creation of stable devices in CuInSe₂ Crystals, Science 258 (1992) 271-274." should read -- Cahen, D.; Gilet, J. M.; Schmitz, C.; Chernyak, L.; Gartsman, K.; Jakubowicz, A., Room-Temperature, electric field induced creation of stable devices in CulnSe₂ Crystals, Science 258 (1992) 271-274.--

"El Bouchairi, B.; Bemedé, J.C.; Burgaud, P., Propeties of Ag_{2-x}Se_{1+x/n}-Si diodes, Thin Solid Films 110 (1983) 107-113." should read -- El Bouchairi, B.; Bernede, J.C.; Burgaud, P., Properties of Ag_{2-x}Se_{1+x/n}-Si diodes, Thin Solid Films 110 (1983) 107-113. --

"Fadel, M., Switching ph nom non in evaporated S -Ge-As thin films of amorphous chalcogenid glass, Vacuum 44 (1993) 851455." should read -- Fadel, M., Switching phe-nomenon in evaporated Se-Ge-As thin films of amorphous chalcogenide glass, Vacuum 44 (1993) 851-855.--

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Title page (cont'd).

"Fadel, M.; El-Shari, H.T., Electrical, thermal and optical properties of Se75Ge7Sb18, Vacuum 43 (1992) 253-275." should read --Fadel, M.; El-Shari, H.T., Electrical, thermal and optical properties of Se75Ge7Sb18, Vacuum 43 (1992) 253-257. --

"Hegab, N.A.; Fadel, M.; Sedeek, K., Memory switching phenomena in thin films of chalcogenide semiconductors, Vacuum 45 (1994) 459-462." should read -- Hegab, N.A.; Fadel, M.; Sedeek, K., Memory switching phenomena in thin films of chalcogenide semiconductors, Vacuum 45 (1994) 459-462. --

"Hosokawa, S., Atomic and electronic structures of glassy GexSel-x around the stiffness threshold composition, J. Optoelectronics and Advanced Materials 3 (2001) 199-214." should read -- Hosokawa, S., Atomic and electronic structures of glassy GexSel-x around the stiffness threshold composition, J. Optoelectronics and Advanced Materials 3 (2001) 199-214. --

"Matsushita, T.; Yamagami, T.; Okuda, M., Polarized memory effect observed on Se-SnO₂ system, Jap. J. Appl. Phys. 11 (1972) 1657-1662." should read --Matsushita, T.; Yamagami, T.; Okuda, M., Polarized memory effect observed on Se-SnO₂ system, Jap. J. Appl. Phys. 11 (1972) 1657-1662.--

"Prakash, S.; Asokan, S.; Ghare, D.B., Easily reversible memory switching in Ge-As-Te glasses, J. Phys. D: Appl. Phys 29 (1996) 2004-2008." should read -- Prakash, S.; Asokan, S.; Ghare, D.B., Easily reversible memory switching in Ge-As-Te glasses, J. Phys. D: Appl. Phys. 29 (1996) 2004-2008. --

"Rahman, S.; Silvarama Sastry, G., Electronic switching in Ge-Bi-Se-Te glasses, Mat. Sci. and Eng. B12 (1992) 219-222." should read -- Rahman, S.; Silvarama Sastry, G., Electronic switching in Ge-Bi-Se-Te glasses, Mat. Sci. and Eng. B12 (1992) 219-222.--

"Tregouet, Y.; Bernede, J.C., Silver movements in Ag₂Te thin films: switching and memory effects, This Solid Films 57 (1979) 49-54." should read -- Tregouet, Y.; Bernede, J.C., Silver movements in Ag₂Te thin films: switching and memory effects, This Solid Films 57 (1979) 49-54. --

"Uemura, O.; Kameda, Y.; Kokai, S.; Satow, T., Thermally induced crystallization of amorphous Ge0.4Se0.6, J. Non-Cryst. Solids 117-118 (1990) 219-221." should read -- Uemura, O.; Kameda, Y.; Kokai, S.; Satow, T., Thermally induced crystallization of amorphous Ge0.4Se0.6, J. Non-Cryst Solids 117-118 (1990) 219-221. --

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Column 1,

Line 50, "-of" should read -- of --

Column 8,

Line 59, "comprising least" should read -- comprising at least --

Signed and Sealed this

Nineteenth Day of April, 2005



JON W. DUDAS
Director of the United States Patent and Trademark Office